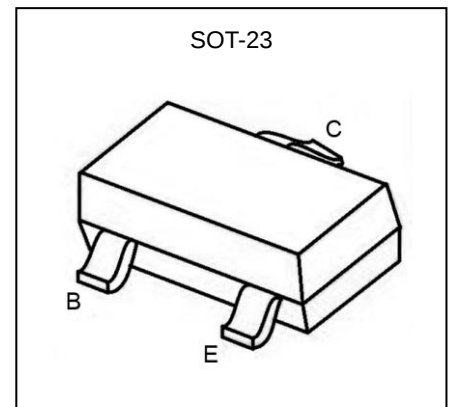


MMBT2907A Transistor(PNP)

Feature

- Epitaxial Planar Die Construction
- Complementary NPN Type Available(MMBT2222A)

Marking: 2F



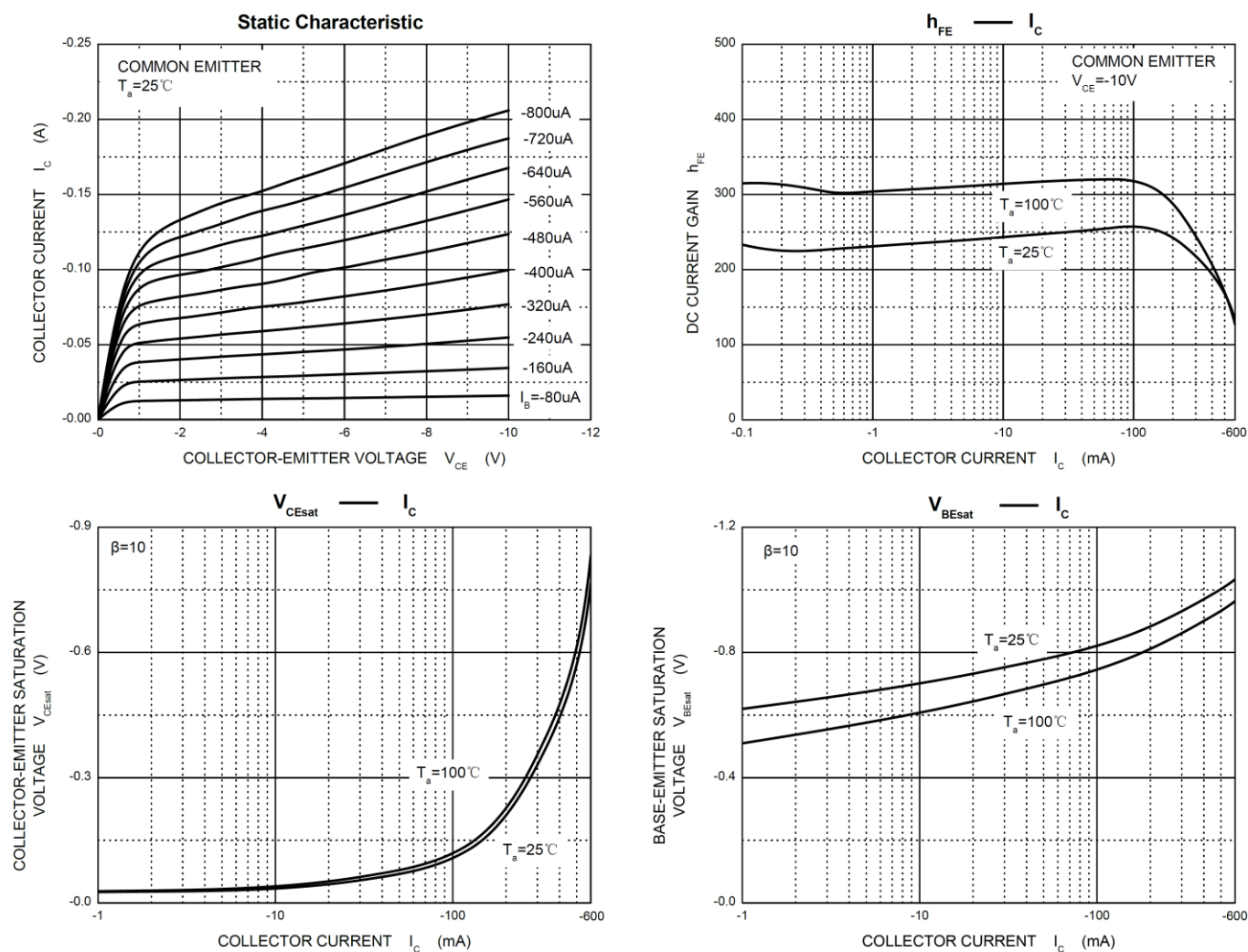
MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

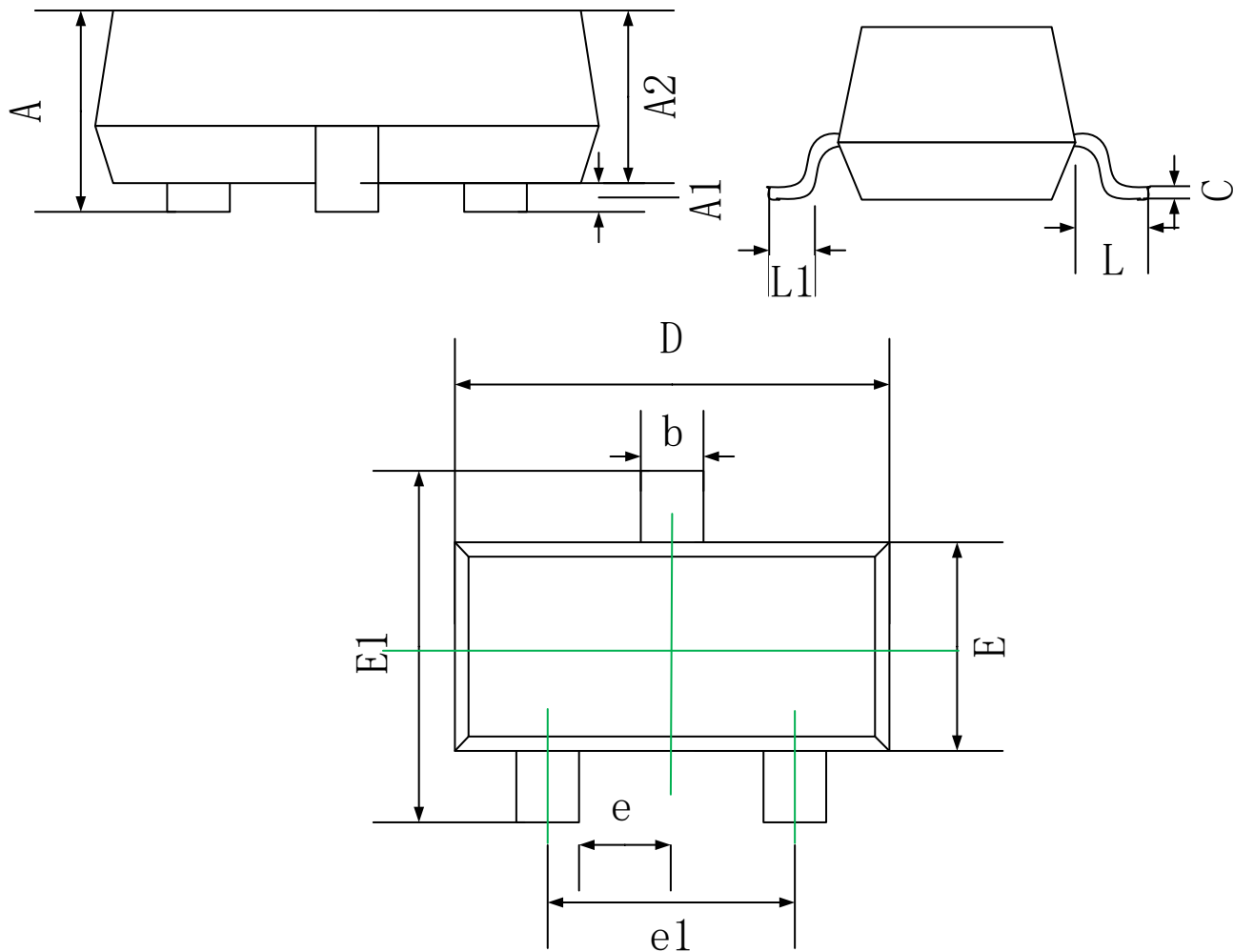
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.6	A
Power Dissipation	P_d	0.625	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-100\mu\text{A}$, $I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}$, $I_E=0$		-100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=-60\text{V}$, $I_B=0$		-100	nA
Base cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$		-100	nA
DC current gain	h_{FE}	$V_{CE}=-10\text{V}$, $I_C=-150\text{mA}$	200	300	
		$V_{CE}=-10\text{V}$, $I_C=-0.1\text{mA}$	40		
		$V_{CE}=-10\text{V}$, $I_C=-500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$		-1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$		-2.0	V
Transition frequency	f_T	$V_{CE}=-20\text{V}$, $I_C=-20\text{mA}$, $f=100\text{MHz}$	250		MHZ

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50